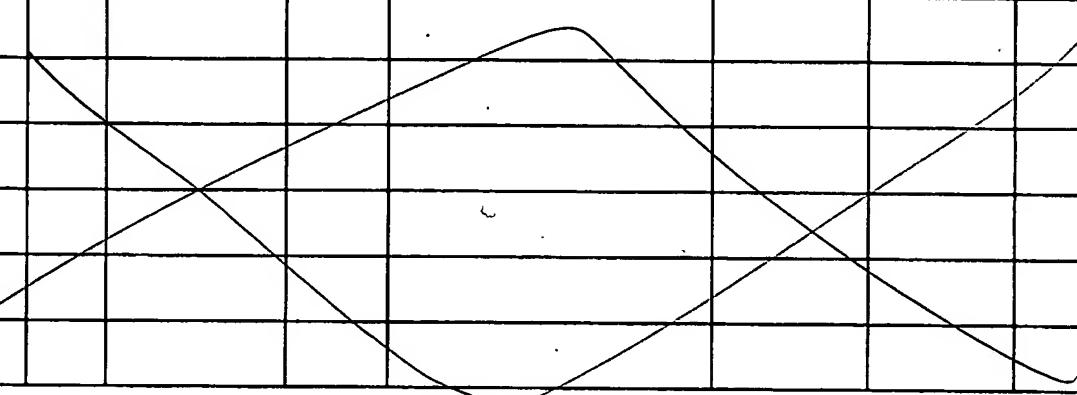
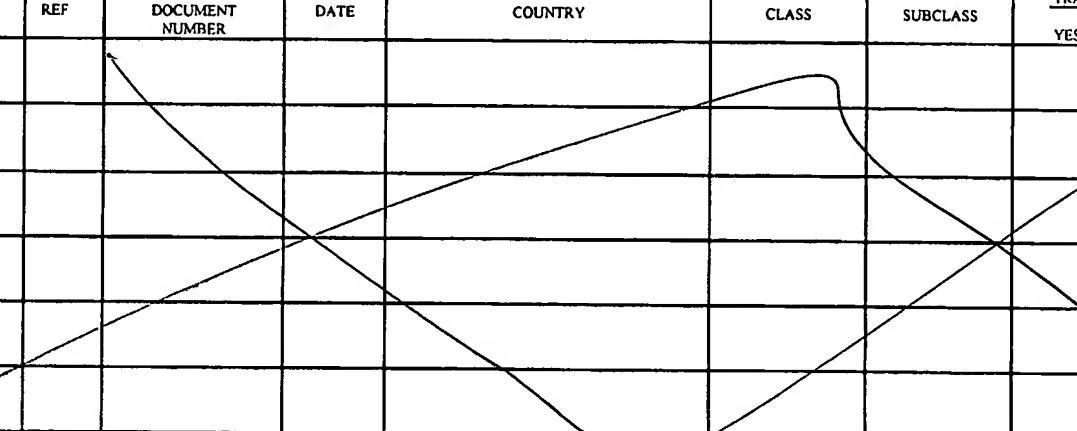
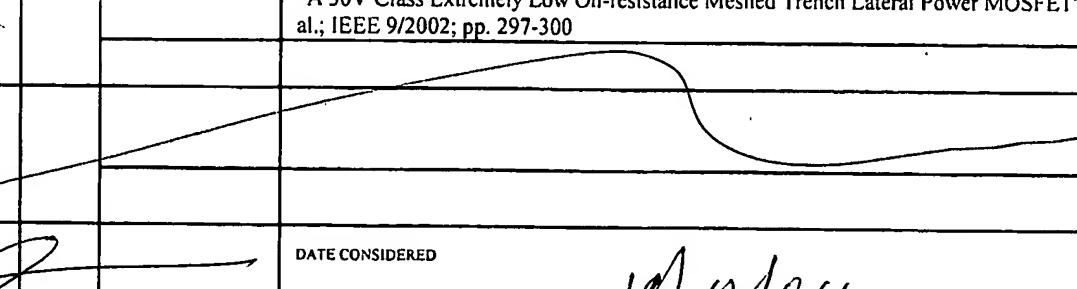


10/720,738

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)			Docket Number (Optional) FUJI:280		SERIAL NO.: NEW APPLICATION		
			APPLICANT(s) Akio SUGI et al.				
			FILING DATE: November 24, 2003			Group Art Unit	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SL	US	2002/0179967	12/02	Fujishima	257	330	
							
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
							
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
SL			"A 30V Class Extremely Low On-resistance Meshed Trench Lateral Power MOSFET"; A SUGI et al.; IEEE 9/2002; pp. 297-300				
EXAMINER			DATE CONSIDERED				

***EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.